

## EXPERIMENT X. BASIC AND STANDARD TTL INVERTERS

### I. Introduction

#### I.I Objectives

In this experiment, you will analyze and compare the voltage transfer characteristics (VTC) and the dynamic response of the basic and standard TTL inverter. You will use Visual Engineering Environment (VEE) for controlling the laboratory instruments

- DC power supply (Agilent E3631A) and
- Digital multimeter (Agilent 34401A) for sending and receiving data. You will manipulate this data to display the VTC of TTL inverters.

### II. Preliminary Work

- 1) Read Chapter 7 (Transistor-Transistor Logic [TTL]) of **Digital Integrated Circuits** by T. A. Demassa and Z. Ciccone.
- 2) Read your **EE312 course notes** for information on TTL inverters.

3) Consider the basic TTL inverter given in Fig. 1. Assume that  $V_{BE(FA)}=0.7$  V,  $V_{BE(SAT)}=0.8$  V,  $V_{CE(SAT)}=0.2$  V,  $V_{BC(RA)}=0.7$  V,  $\beta_F=50$ ,  $\beta_R=0.1$ . Use  $\sigma_0=0.8$  (saturation parameter of  $Q_0$ ) for the output low state.

- i) Find the operation mode of each BJT and  $I_{IN}$ ,  $I_{RB}$ ,  $I_{RC}$ ,  $I_{B2}$  when  $V_{in}=0$  V and  $V_{in}=5$  V.
- ii) Sketch the **voltage transfer characteristics** by finding  $V_{OL}$ ,  $V_{OH}$ ,  $V_{IL}$ ,  $V_{IH}$ .
- iii) Find the **noise margins**.
- iv) Find the **maximum fanout**. What is the limiting case for determining the fan-out limit of this circuit?

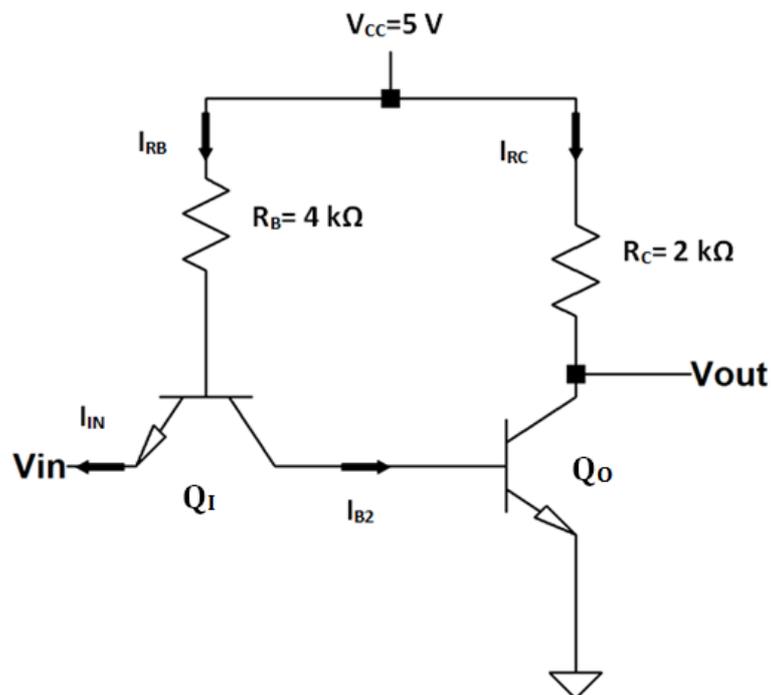


Fig. 1: The schematic view of a basic TTL inverter

4) What are the **advantages** of the basic TTL inverter when compared with the basic BJT inverter (RTL inverter that you also constructed in Experiment 2)? What are the limitations of the circuit?

- 5) Consider the standard TTL inverter given in Fig. 2. Assume that  $V_{BE(FA)}=0.7\text{ V}$ ,  $V_{BE(SAT)}=0.8\text{ V}$ ,  $V_{CE(SAT)}=0.2\text{ V}$ ,  $V_{BC(RA)}=0.7\text{ V}$ ,  $\beta_F=50$ ,  $\beta_R=0.1$ ,  $V_{DIODE(ON)}=0.7\text{ V}$ . Use  $\sigma_0=0.8$  (saturation parameter of  $Q_0$ ) for the output low state.
- Sketch the **voltage transfer characteristics** by finding  $V_{OL}$ ,  $V_{OH}$ ,  $V_{IL}$ ,  $V_{IH}$ ,  $V_{IB}$ ,  $V_{OB}$ .
  - Find the **noise margins**.
  - Find the **maximum fanout**. What is the limiting case for determining the fan-out limit of this circuit?
  - Find the **average power dissipation** when there is no load.

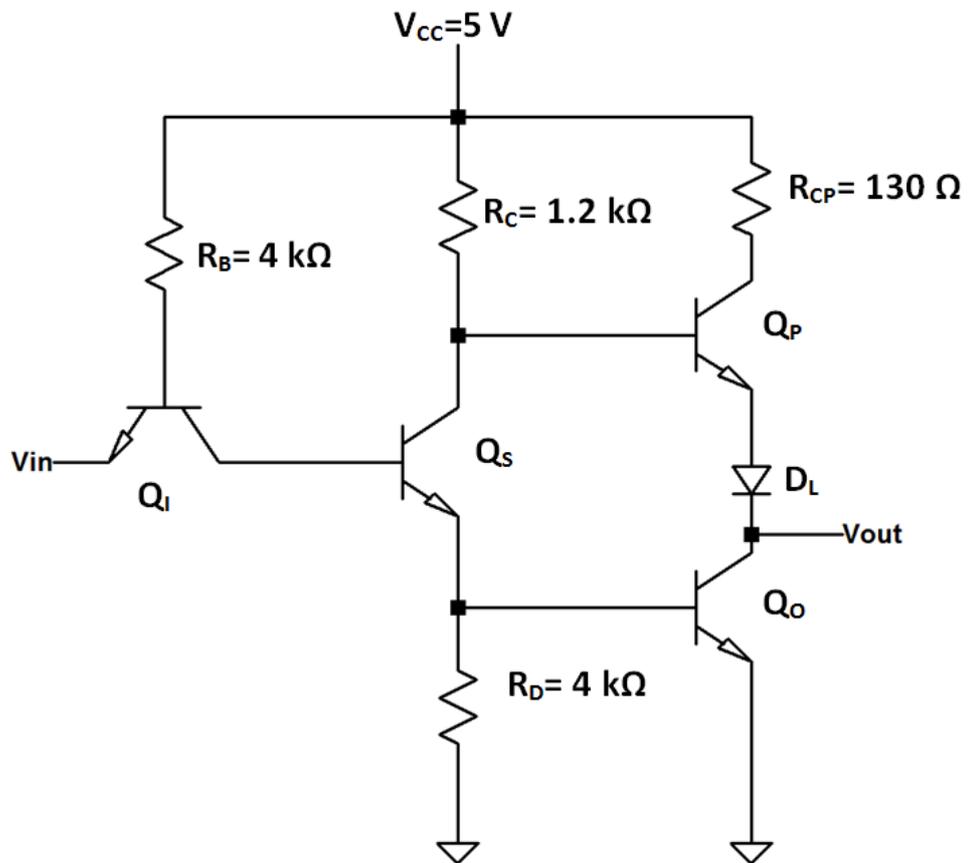


Fig. 2: The schematic view of a standard TTL inverter

- What are the **advantages** of the standard TTL inverter when compared with the basic TTL inverter?
- Read the **Displaying Voltage Transfer Characteristics with VEE** section in **Experiment 2**. Bring the **Experiment 2 manual** with you when you come to the laboratory.

### III. Experimental Work

#### a) Basic TTL Inverter

Fig. 3 and Fig. 4 show the schematic view of a TTL inverter circuit and the internal diagram of CA3046 BJT array chip. Construct the TTL inverter circuit by using **two npn BJTs** in CA3046. Connect **pin 13** to **ground**.

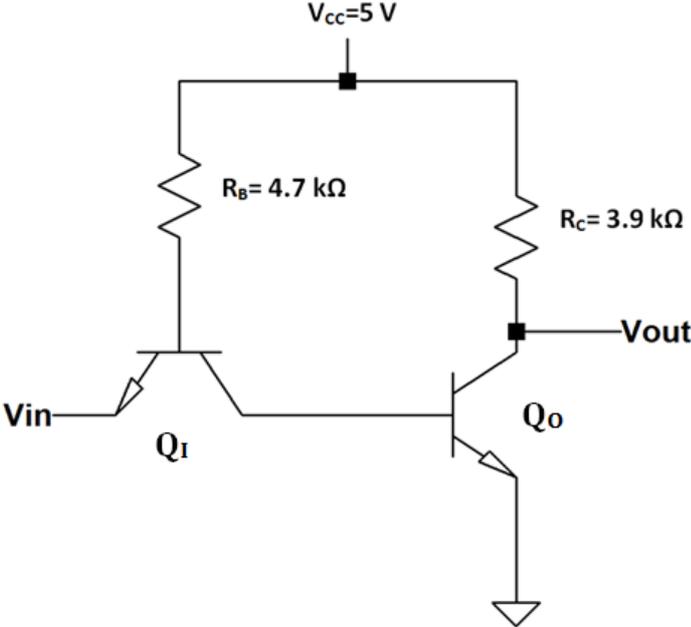


Fig. 3: The schematic view of a basic TTL inverter

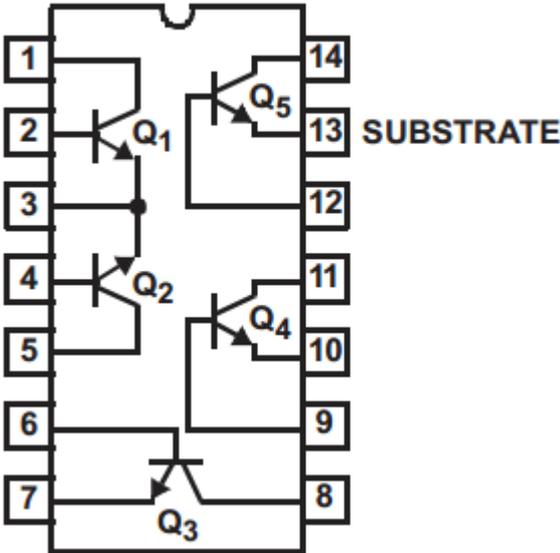


Fig. 4: Pin diagram for CA3046 BJT array chip

- 1) Use the **multimeter** in **voltage measuring mode** to find the operation modes of the BJTs for  $V_{IN} = 0V$  and  $V_{IN} = 5V$ .
- 2) Obtain the **voltage transfer characteristics** of the basic TTL inverter with the help of **VEE**. Set  $V_{CC} = 5V$ . **Sweep** the  $V_{IN}$  from **0 V** to **5 V** in **0.05 V** steps.
- 3) Find the critical voltages,  $V_{IL}$ ,  $V_{IH}$ ,  $V_{OL}$ ,  $V_{OH}$  and **noise margins**. Why the difference between  $V_{IL}$  and  $V_{IH}$  is small? Why is the low noise margin much smaller than the high noise margin?
- 4) Measure the emitter current of Q1 for  $V_{IN} = 0$  and  $V_{IN} = 5V$ .
- 5) Explain the operation of this inverter.
- 6) What is the limiting case for determining the fan-out limit of this circuit? Comment briefly on what is expected when  $V_{OUT} = V_{OH}$ .
- 7) Find the fan-out limit of the circuit for  $V_{OUT} = V_{OL}$ . Connect the **circuit input** to  $V_{CC}$  and connect a **potentiometer between** the **output** and  $V_{CC}$ . Change the potentiometer resistance and record the current through the resistor when  $V_{OUT}$  exceeds the acceptable low level voltage.
- 8) Ground the circuit input and connect a resistance between the output and ground with a value equivalent to the **fan-out of 1**. Measure the output voltage and comment on the result. What is the limitation of this circuit? How can the circuit be improved for a reasonable fan out limit?
- 9) In this part, we will measure the rise and fall times of the basic TTL inverter with **VEE**. Disconnect the input of the circuit from the power supply. Connect a **100 pF capacitor** between the output and ground. Set the output of the function generator to **High Z**. Connect the input of the circuit to the output of the function generator and set the waveform to a square wave with **5 V<sub>PP</sub>** amplitude and **2.5 V offset** at a frequency of **1 kHz**. Connect the **channel 1** of the oscilloscope to the **output**.

Since there are two types of oscilloscope in the laboratory and their drivers are not the same, we will use different **VEE** configurations for them.

### **i) Configuration for 54645D Oscilloscope Using Plug & Play Drivers**

- From **Instrument Manager**, click on **HP54645D** and then **PNP** button and place the **Plug & Play Driver** in the work area.
- Double click on the **<Double-Click to Add Operation>** bar of the driver. Select **WaveformArray\_Q** under **Waveform**. From the **Panel** tab, select **Analog Channel 1**.
- Add an **X vs Y Plot** object. Connect **W\_Time** and **W\_Volt** data output pins of the Plug & Play Driver to the **XData** and **YData1** pins, respectively.

## ii) Configuration for MSO-X2012A Oscilloscope Using IVI Drivers

- From **Instrument Manager**, click on **MSOX2012A** and then **IVI** button and place the **IVI Driver** in the work area.
- Double click on the **<Double-Click to Add Operation>** bar of the driver. Select **CreateInstance** and click **OK**. Click **OK** in the opened Edit "CreateInstance" window.
- Double click on the **<Double-Click to Add Operation>** bar of the driver. Select **Initialize** and click **OK**. Enter **simulate=false** into the **OptionString** field and click **OK**.
- Double click on the **<Double-Click to Add Operation>** bar of the driver. Select **Channels** → **Item(Name)** → **FetchWaveform** and enter **channel1** into the **Name** field.
- The input pins of the driver should be connected. Hence, add a **Real64 constant** and a **Real64 Array constant** in the work area. Connect the data output pin of **Real64 Array** to the **WaveformArray input pin** of the driver. Connect data output pin of **Real64** to the **InitialX** and **Xincrement input pins** of the driver. The values of Real64 constant objects are not important.
- Place an **AllocReal64** object in the work area. Add two **data input pins** which are **From** and **Through**. Enter **50000** as the size.
- Add a **Formula** object. Add an additional **data input, B**. Enter **A+49999\*B** into the formula box. Connect the **InitialX data output pin** of the driver to **A pin** of **Formula**. Connect the **Xincrement data output pin** of the driver to **B pin** of **Formula**.
- Connect the **Return data output pin** of **Formula** to **Through pin** of the **AllocReal64** object. Connect the **InitialX data output pin** of the driver to **From pin** of the **AllocReal64** object.
- Add an **X vs Y Plot** object. Connect **Array pin** of **AllocReal64** to the **XData** pin. Connect the **WaveformArray output pin** of the IVI driver to the **YData1** pin.

- 10) Run the VEE program and measure the **rise** and **fall times** of the output.
- 11) You can interpolate the data if necessary. For this purpose, click on **X vs Y Plot** object. From the **Properties** box, change **MarkerInterpolat** value to **True** under **Markers**.

## b) 74LS00 TTL NAND Gates

Fig. 5 shows the pin diagram of 74LS00 and the internal structure of one of the NAND gates. Insert 74LS00 IC into your breadboard. Connect **pin 14 to 5 V** and **pin 7 to ground**. Connect a **10 nF capacitor between  $V_{CC}$  and ground**.

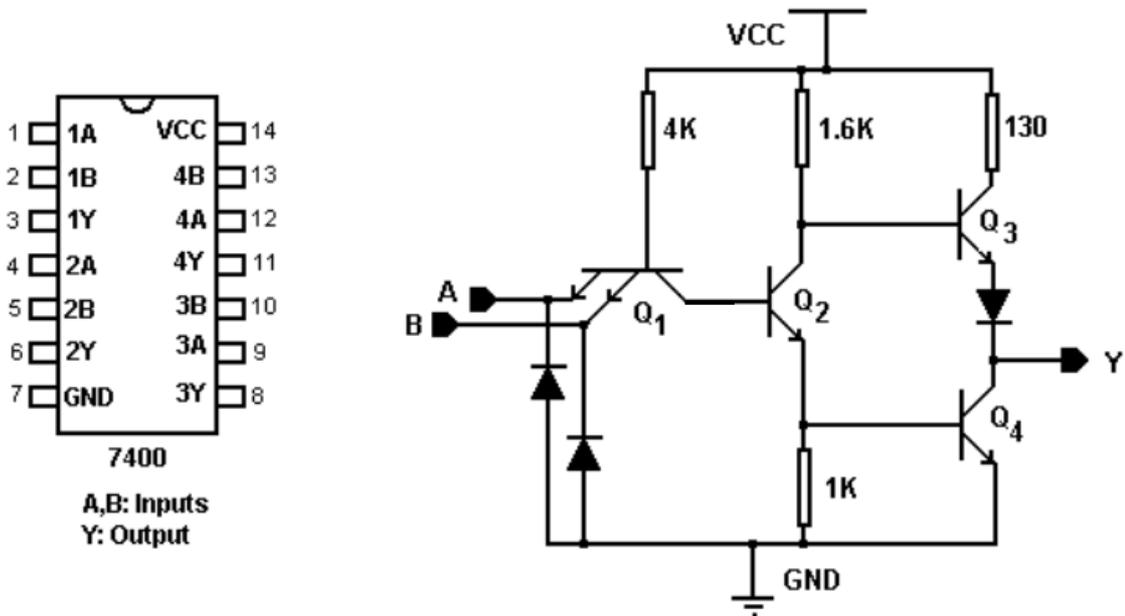


Fig. 5: The pin diagram of 74LS00 and the internal structure of one of the NAND gates

- 1) Leave the other pins unconnected and measure the **voltages** on **pins 1,2,3,4,5,6,8,9,10,11,12, and 13**. Comment on the results.
- 2) Now use one of the NAND gates in the IC. **Short circuit the two inputs** and obtain the **voltage transfer characteristics** with the help of **VEE**. Set  $V_{CC}=5\text{ V}$ . **Sweep** the  $V_{IN}$  from **0 V to 5 V** in **0.05 V** steps.
- 3) Find the critical voltages,  $V_{IL}$ ,  $V_{IH}$ ,  $V_{OL}$ ,  $V_{OH}$  and **noise margins**.
- 4) Measure the input currents under high and low level input conditions.
- 5) Connect the inputs to ground. Connect a resistor equivalent to a **fan-out of 15** between the output and ground and measure the output voltage. Compare the fanout limitation of this circuit (schematics shown above) with the circuit in Part 1 of Experimental Work (TTL inverter). Comment on the result by stating the reason for higher fan-out in this circuit.

- 6) Disconnect the resistor connected at the output. Connect a **100 pF capacitor** between the output and ground. Apply a **5 V<sub>pp</sub> square wave** of **1 kHz** frequency and **2.5 V offset** at the input and measure the **rise** and **fall times** of the NAND gate using VEE and compare them with those measured in **Part a** of Experimental Work. State the reasons of any differences you observe in the switching times of this circuit and the circuit in **Part a**.